

GPTP5125

PHASE CONTROLLED SCR

High reliability operation
DC power supply
AC drives

VOLTAGE UP TO	4200 V
AVERAGE CURRENT	1250 A
SURGE CURRENT	15 kA

BLOCKING CHARACTERISTICS

Characteristic	Conditions	Value
V _{RRM}	Repetitive peak reverse voltage	4200 V
V _{RSM}	Non-repetitive peak reverse voltage	4300 V
V _{DRM}	Repetitive peak off-state voltage	4300 V
I _{DRM}	Repetitive peak off-state current, max.	V _{DRM} , single phase, half wave, T _j = T _{jmax} 200 mA
I _{IRRM}	Repetitive peak reverse current, max.	V _{RRM} , single phase, half wave, T _j = T _{jmax} 200 mA

ON-STATE CHARACTERISTICS

I _{T(AV)}	Average on-state current	Sine wave, 180° conduction, Th = 55 °C	1250 A
I _{T(RMS)}	R.M.S. on-state current	Sine wave, 180° conduction, Th = 55 °C	1963 A
I _{TSM}	Surge on-state current	Non rep. half sine wave, 50 Hz, V _R = 0 V, T _j = T _{jmax}	15 kA
I ² t	I ² t for fusing coordination		1125 kA ² s
V _{T(TO)}	Threshold voltage	T _j = T _{jmax}	0,90 V
r _T	On-state slope resistance	T _j = T _{jmax}	0,565 mΩ
V _{TM}	Peak on-state voltage, max	On-state current I _T = 2000 A, T _j = T _{jmax}	2,03 V
I _H	Holding current, max	T _j = 25 °C	80 mA
I _L	Latching current, typ	T _j = 25 °C	500 mA

TRIGGERING CHARACTERISTICS

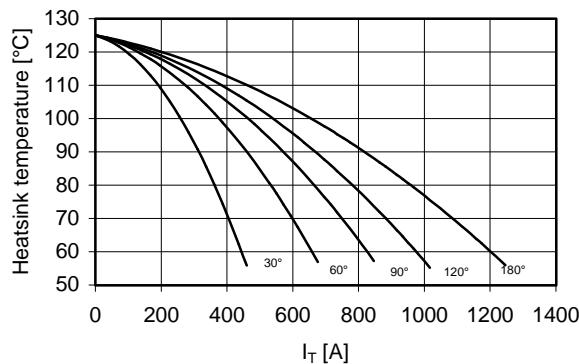
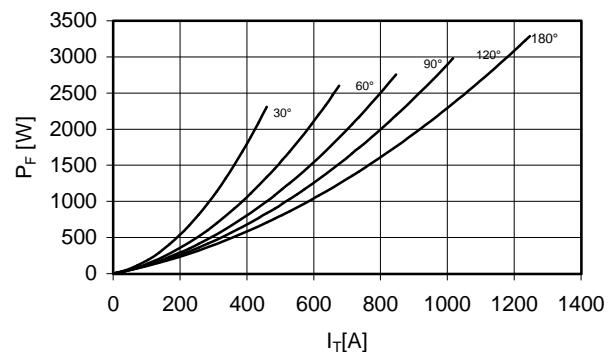
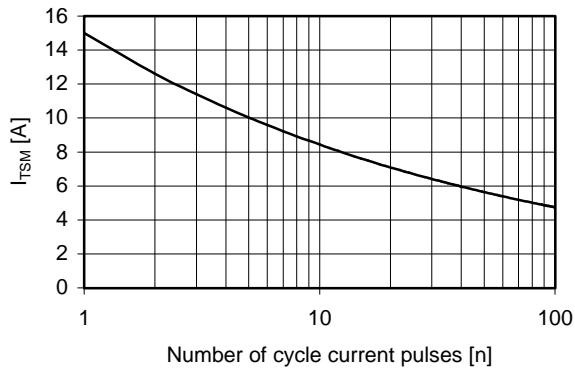
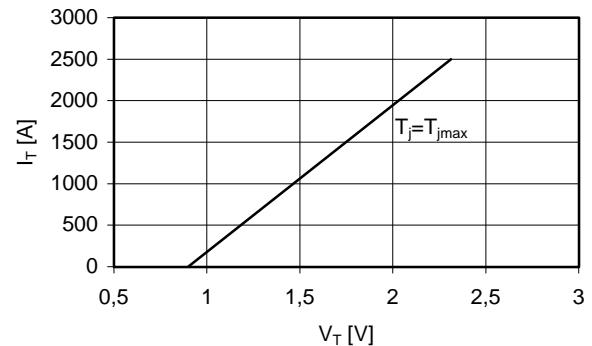
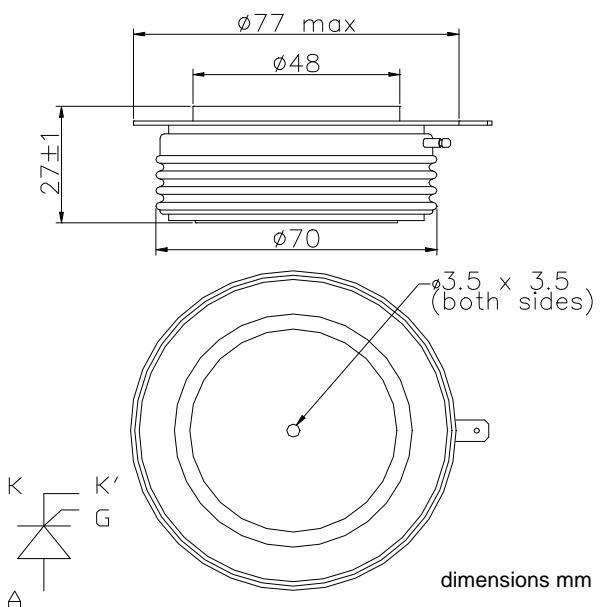
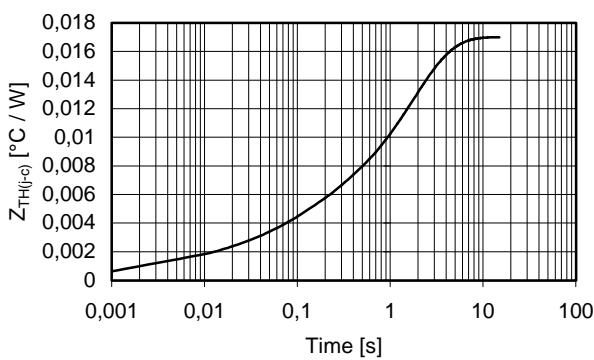
V _{GT}	Gate trigger voltage	T _j = 25 °C, V _D = 5 V	3 V
I _{GT}	Gate trigger current	T _j = 25 °C, V _D = 5 V	400 mA
V _{GD}	Non-trigger voltage	V _D = 67% V _{RRM} , T _j = T _{jmax}	0,3 V
P _{GM}	Peak gate power dissipation	Pulse width 1 ms	20 W
P _{G(AV)}	Average gate power dissipation		3 W
I _{FGM}	Peak gate current		10 A
V _{FGM}	Peak gate voltage (forward)		12 V
V _{RGFM}	Peak gate voltage (reverse)		10 V

SWITCHING CHARACTERISTICS

di/dt	Critical rate of rise of on-state current	Non rep. - T _j = T _{jmax}	1000 A/μs
dV/dt	Critical rate of rise of off-state voltage	T _j = T _{jmax}	1000 V/μs
t _q	Turn-off time, typ	T _j = T _{jmax} , I _T = 2000 A, di/dt = -5 A/μs VR = 200 V, VD = 67% V _{DRM} , dV/dt = 20 V/μs	600 μs

THERMAL AND MECHANICAL CHARACTERISTICS

R _{th(j-c)}	Thermal resistance (junction to case)	Double side cooled	0,017 °C/W
R _{th(c-h)}	Thermal resistance (case to heatsink)	Double side cooled	0,004 °C/W
T _{jmax}	Max operating junction temperature		125 °C
T _{stg}	Storage temperature		-40 / 140 °C
F	Clamping force ± 5%		22 kN
	Mass		600 g

Current rating - sine wave

Power loss - sine wave

**Maximum surge current
d.s. cooled**

On-state voltage drop

Thermal impedance (j-c)


In the interest of product improvement Green Power Solutions reserves the right to change any specification given in this data sheet without notice.